Amendments to the Specification:

Please amend the specification as follows:

Please replace the paragraph starting at page 6, line 6 with the following rewritten paragraph:

Preferably, the density, i.e., the concentration, of the ozonized water is 10 to 60 ppm and the density, i.e., the concentration, of the hydrofluoric acid is 0.5 to 2%.

Please replace the paragraph starting at page 6, line 8 with the following rewritten paragraph:

By cleaning within the above-mentioned density, i.e., the concentration, range, the oxidation treatment time and cleaning time can be adjusted easily.

Please replace the paragraph starting at page 6, line 25 with the following rewritten paragraph:

Fig. 4 is a schematic diagram showing an example of a single-wafer ~~sinle-wafer~~ spin cleaning system apparatus which executes the cleaning method of the present invention;

Please replace the paragraph starting at page 10, line 1, with the following rewritten paragraph:

In case of spraying, the cleaning method of the present invention can be executed with a single-wafer ~~sinle-wafer~~ spin cleaning system apparatus shown in Fig. 4.

Please replace the paragraph starting at page 10, line 4, with the following rewritten paragraph:

In the single-wafer ~~sinle-wafer~~ spin cleaning system apparatus, a silicon wafer 2 is disposed on a rotation table 3 in a spin cup 1 through a holding pin 4. The rotation table 3 is rotated by a driving force of a motor 6 through a drive shaft 5 connected through a bottom face.

Please replace paragraph starting at page 10, line 14 with the following rewritten paragraph:

Although the density, i.e., the concentration, of the ozonized water is not restricted, it is desired to be 10 to 60 ppm from viewpoints of oxidation treatment time adjustment.

Please replace paragraph starting at page 10, line 17 with the following rewritten paragraph:

The density, i.e., the concentration, of hydrofluoric acid is desired to be 0.5 to 2% from viewpoints of cleaning time adjustment.

Please replace paragraph starting at page 16, line 27 with the following rewritten paragraph:

This specimen wafer was oxidized for 30 seconds with 20 ppm ozonized water using the single-wafer ~~sinle-wafer~~ spin cleaning system apparatus shown in Fig. 4 and washed by changing the cleaning time using 1% hydrofluoric acid.